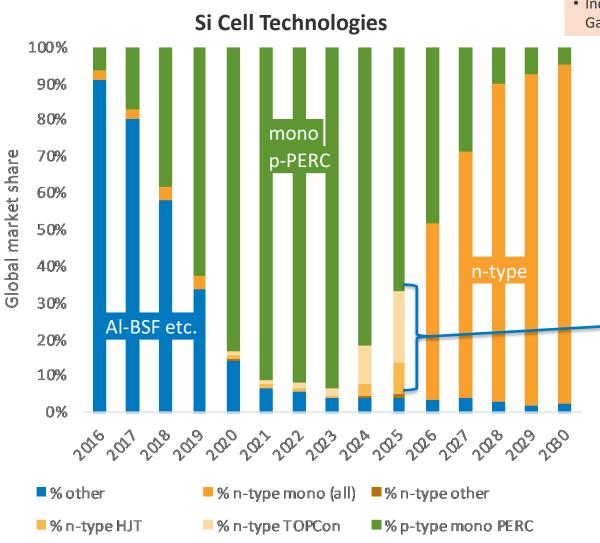


# Cell Technologies Evolution

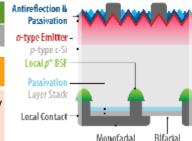


### p-type

**PERC** (Passivated Emitter and Rear Cell)

### **Drivers & Benefits**

- Largest market share and longest history
- Monofacial and bifacial options
- Industry transitioned from Boron to Gallium doping to mitigate degradation

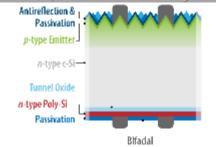


### Potential Risks & Challenges

- Current production cells close to practical efficiency limits - further improvements difficult
- Bifaciality is slightly lower compared to TOPCon/SHJ

### n-type

### **TOPCon** (Tunnel Oxide Passivating Contact)



### **Drivers & Benefits**

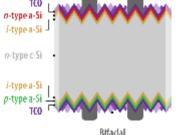
- Inherently bifacial
- Most easily adapted from existing PERC capacity
- Slight efficiency and bifaciality advantage over PERC

### **Potential Risks & Challenges**

 Newer technology than SHJ - less production history, but fundamentally compatible with the conventional Si solar cell production process

M. Woodhouse, PVRW 2023





### **Drivers & Benefits**

- Superior surface passivation quality improves carrier lifetime and increases cell voltage even further (750 mV)
- Typically, the highest bifaciality and slight efficiency advantage over PERC

### **Potential Risks & Challenges**

- Process temperature limited to <200°C, and this impacts metallization and interconnect technologies and costs
- Substantially different manufacturing process
- Higher tool costs

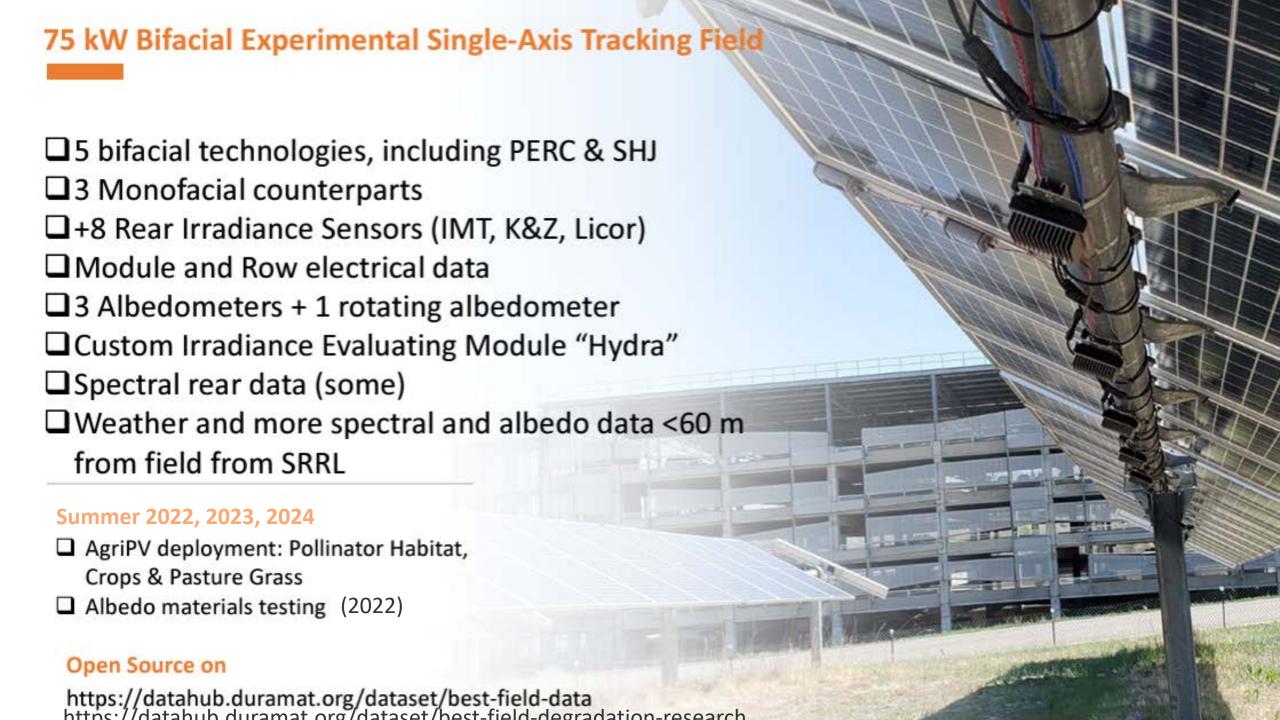
Jarett Zuboy et al DuraMAT Tech Scouting 2022



### 2019-2024



Open source data: <a href="https://datahub.duramat.org/dataset/best-field-data">https://datahub.duramat.org/dataset/best-field-data</a>
<a href="https://datahub.duramat.org/dataset/best-field-degradation-research">https://datahub.duramat.org/dataset/best-field-degradation-research</a>



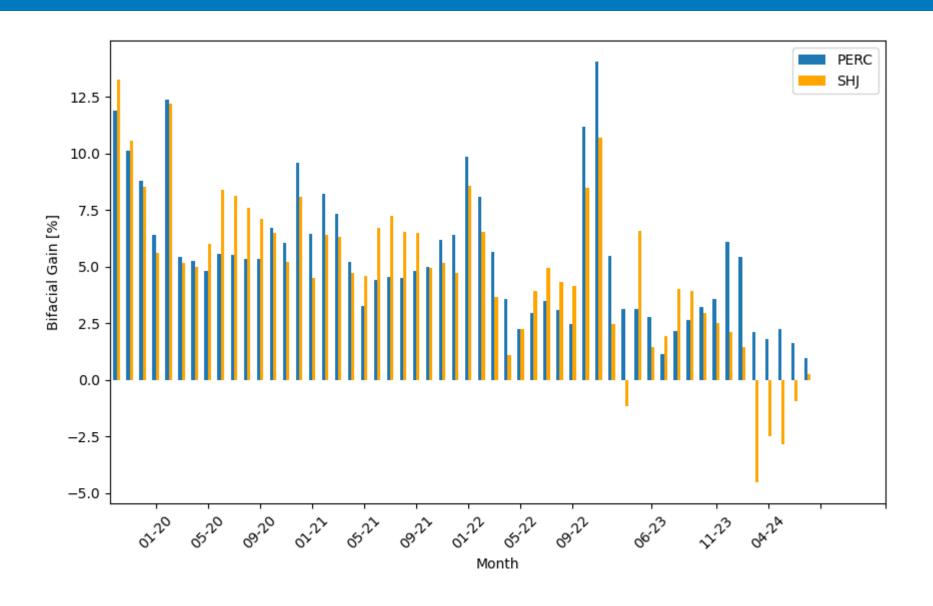
## Technologies under discussion

	Manufacturer A Prism	Manufacturer B Longi	Manufacturer C	Manufacturer D	Manufacturer E Sunpreme
Technology	pPERC	pPERC	pPERC	mc-pPERC	HJT
Back Surface			Glass		
Half or Full Cell	Full	Full	Half	Half	Half
JB Location	Тор	Тор	Center	Center	Center
Encapsulant*	EVA	NA	EVA	NA	NA
Control module available	Yes	Yes	Yes	No	Yes
Monofacial pair available	No	Yes	Yes	Yes	No

## 4.83-year Technology Comparison

\*Grouped by Month PERC bifacial gain: 5.1%; SHJ gain: 5.7% 10 **PERC** 8 Si Heterojunction Bifacial Gain [%] 6 2

## Bifacial energy gain has a downward trend over the years



## Bifacial Gain by year

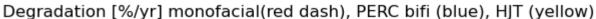
Annual	YEAR1 (partial)	YEAR2	YEAR3	YEAR4	YEAR5	Average over
Bifacial Gain	Oct'19– Jul'20	Aug'20 – Jul'21	Aug'21 - Jul'22	Aug'22 - Jul'23	Aug'23 - Jul'24	4.83 years
Technology A	6.2%	5.0%	3.6%	3.5%	1.5%	4.1%
Technology B	9.1%	8.8%	8.3%	8.2%	5.6%	8.1%
Technology C	4.6%	4.0%	3.2%	2.9%	1.7%	3.3%
Technology D	6.5%	5.6%	5.0%	5.0%	2.7%	5.0%
PERC Gain	6.6%	5.8%	5.0%	4.9%	2.9%	5.2%
Technology E (SHJ)	7.7%	6.9%	5.7%	5.0%	1.9%	5.7%

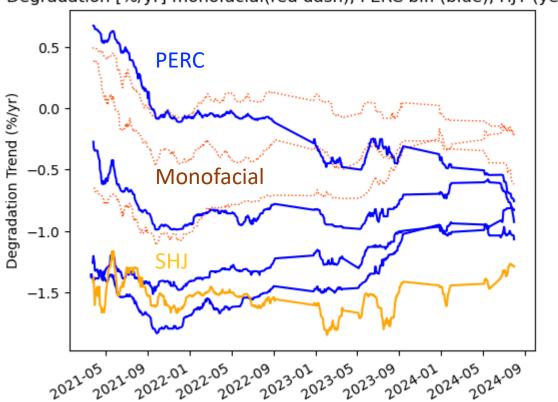
### **PLR Rates**

Degradation Rates % Cumulative 10/2019 to:	8/1/2021	8/1/2022	8/1/2023	8/1/2024	AVG to Date
Technology A	-1.38	-1.32	-1.22	-1.11	
Technology B	0.29	-0.08	-0.14	-0.34	0.04
Technology C	-1.60	-1.51	-1.42	-1.34	-0.94
Technology D	-0.78	-0.86	-0.83	-0.83	
Technology E (SHJ)	-1.30	-1.60	-1.59	-1.46	-1.46
Technology B Mono	0.14	0.06	-0.03	-0.04	
Techhnology C Mono	-0.91	-0.73	-0.71	-0.70	-0.34
Technology D Mono	-0.19	-0.38	-0.33	-0.28	

On average, bifacial PERC and Si-HJT are degrading faster than monofacial counterparts

## Rolling PLR Rate







Year-on year degradation trend, 24-month rolling average

$$PR_n = daily perf.ratio$$

$$Rd_n = \frac{PR_{n+365*2} - PR_n}{\overline{PR}_{vr1}}$$

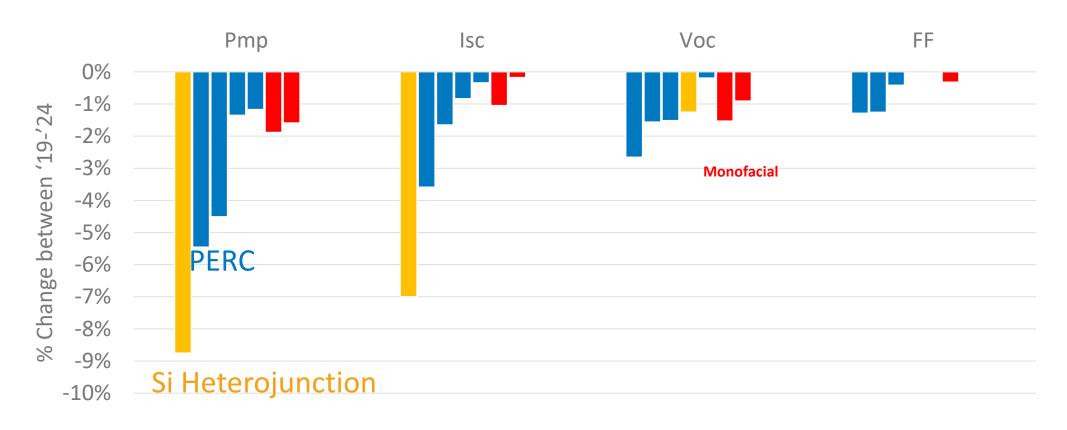
$$\frac{\sum_{365*2}^{1095} Rd_{n:(n+365*2)}}{365*2}$$

Cumulative Average Monofacial: -0.34 %/yr avg

Cumulative Average Bifacial: -0.97%/yr avg Oct 2019-Jul 2024

## IV Parameters Change 2019-2024

Indoor flash-test confirms performance loss; **Isc change** is the dominant difference



## Diagnosis

### **RdTools**

Detects long-term performance trends

Identifies passivation degradation modes, factor

**IV-curve changes** 

Identifies major defects such as broken bypass diodes, disconnected ribbons, shunts, and PID effects.

### EL

Identifies cracks with more detail. Detects Potential Induced Degradation (PID) when checkered patterns are present.

### PL

Assesses passivation quality and helps detect changes in the bulk and surface properties of materials

### Low temp Spectral PL

Can help identify spectral features that could be useful for dopant characterization

### **QE** Measurements

Investigates PID. Determines

FTIR & hand-held gloss meter Identifies UV dosage and degradation on backsheets

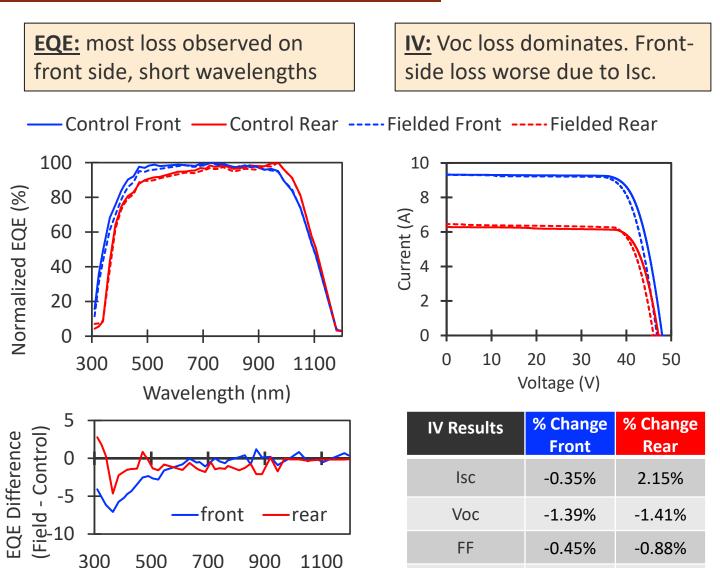
### **Handheld Raman Spectroscopy** Detects changes in encapsulant material due to crosslinking or other chemical changes.

### **Handheld NIR tool**

**Encapsulation characteristics** and changes

pPERC, G/G, Full cell, Top JB, EVA

Wavelength (nm)

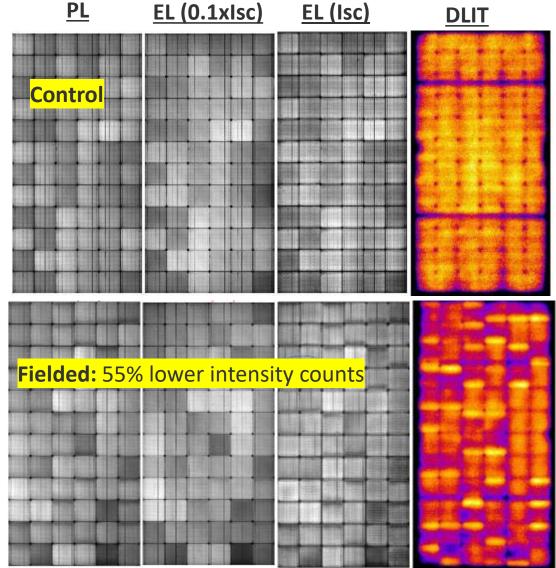


-2.17%

Pmp

-0.13%

**Imaging**: Luminescence intensity decreases to ~55% of the control, consistent with voltage loss. Bands of high recombination become obvious in DLIT.

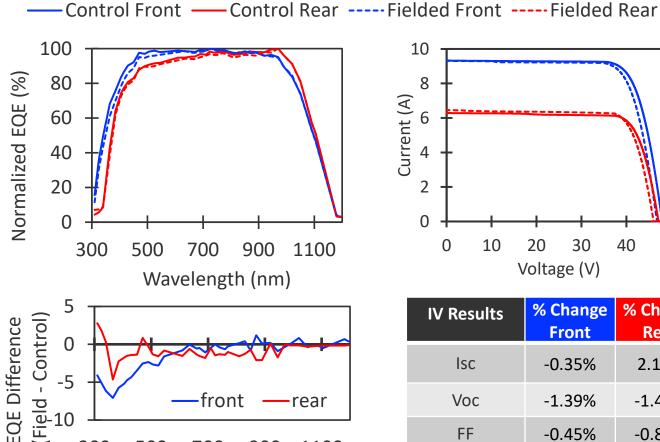


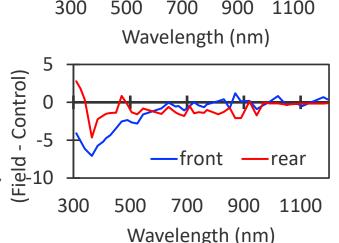
pPERC, G/G, Full cell, Top JB, EVA

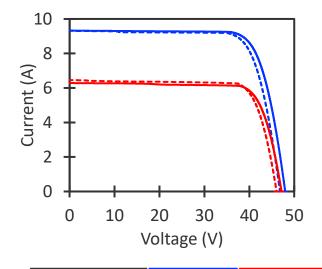
**Summary:** Voc loss from recombination; Optical coupling may impact Isc – loss on front and gain on rear. Minor but unusual resistive pattern affecting FF.

**EQE:** most loss observed on front side, short wavelengths IV: Voc loss dominates. Frontside loss worse due to Isc.

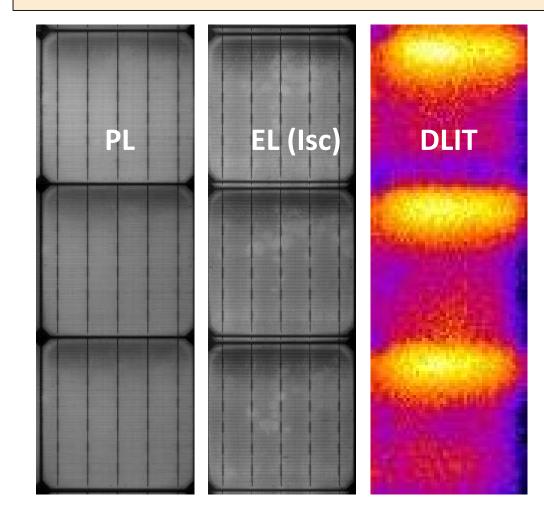
**Imaging**: (zoom into selected area) Dark edge patterns in EL and PL, and hotter DLIT, suggest these are areas with increased carrier recombination.





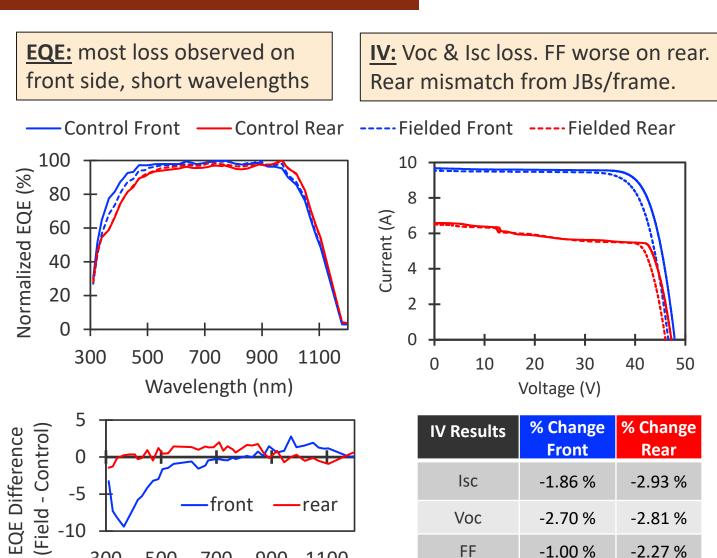


IV Results	% Change Front	% Change Rear	
Isc	-0.35%	2.15%	
Voc	-1.39%	-1.41%	
FF	-0.45%	-0.88%	
Pmp	-2.17%	-0.13%	



pPERC, G/G, Half-cell, Center JB, EVA

300



1100

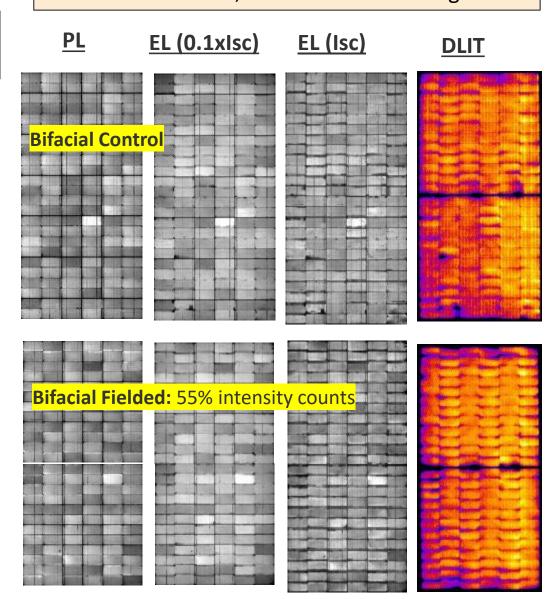
Wavelength (nm)

-5.45 %

Pmp

-7.82 %

**Imaging**: Luminescence intensity decreases to ~55% of the control, consistent with voltage loss.

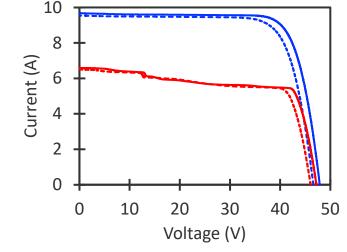


pPERC, G/G, Half-cell, Center JB, EVA

**Summary:** Voc and Isc loss from carrier recombination; Optical coupling may cause additional Isc loss. Resistive grid disconnection near cell edge decreases FF.

**EQE:** most loss observed on front side, short wavelengths **IV:** Voc & Isc loss. FF worse on rear. Rear mismatch from JBs/frame.

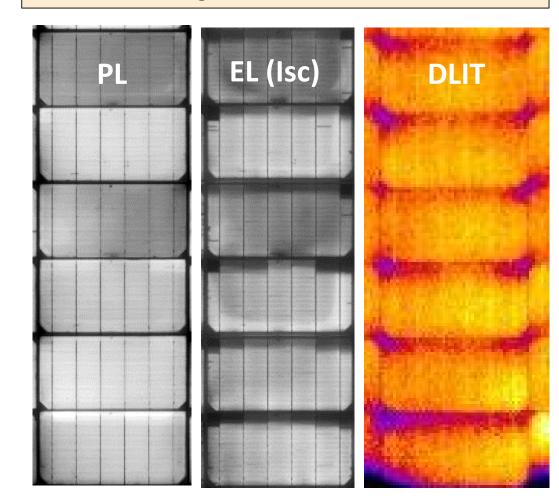
——Control Front ——Control Rear ----- Fielded Front ----- Fielded Rear 100 Normalized EQE (%) 80 60 40 20 300 500 700 900 1100 Wavelength (nm)



: Difference Id - Control)	5 0 -5			—fron	t —	-rear	
EQE	(Fiel	10	300	500	700	900	1100
				Wav	/elengt	:h (nm	)

IV Results	% Change Front	% Change Rear	
Isc	-1.86 %	-2.93 %	
Voc	-2.70 %	-2.81 %	
FF	-1.00 %	-2.27 %	
Pmp	-5.45 %	-7.82 %	

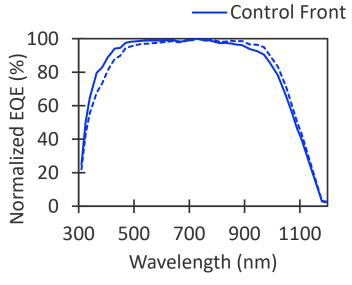
**Imaging**: (zoom into selected area) Edge pattern dark in E,L bright in PL, colder DLIT – suggests high resistance causing FF loss.

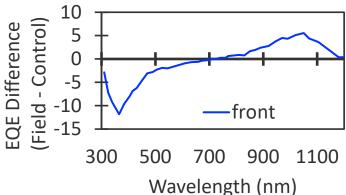


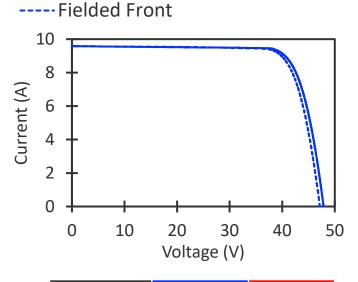
pPERC, G/G, Half-cell, Center JB, EVA

**EQE:** front surface loss - drop at short  $\lambda$ , rel. gain at long  $\lambda$ 

**IV:** Voc loss from recombination, possible passivation loss. Some Rs.

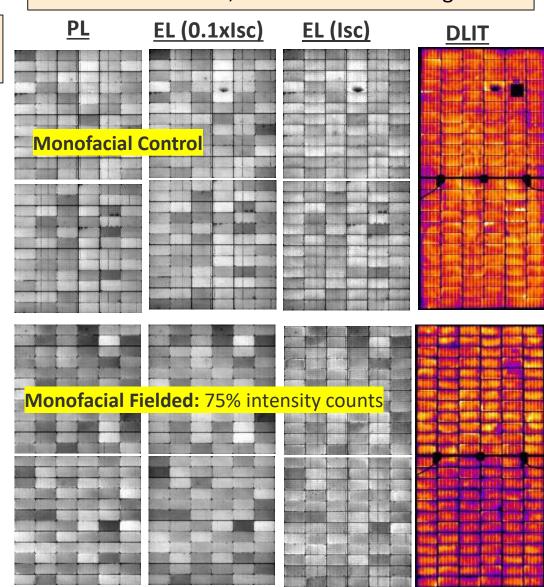






IV Results	% Change Front	% Change Rear	
Isc	-0.30 %	N/A	
Voc	-1.92 %	N/A	
FF	-0.34 %	N/A	
Pmp	-2.54 %	N/A	

Imaging: Luminescence intensity decreases to~75% of the control, consistent with voltage loss.



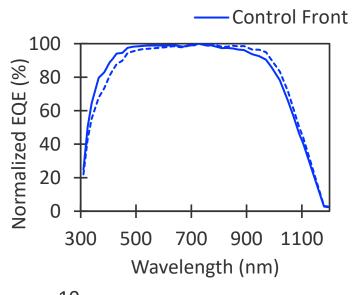
pPERC, G/G, Half-cell, Center JB, EVA

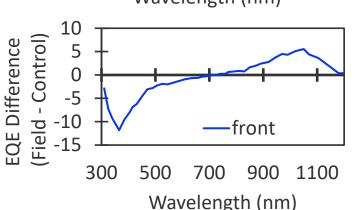
**Summary:** Voc loss from front surface recombination and some inconsistent cell processing observed; Minor resistive issues. Less degradation than bifacial.

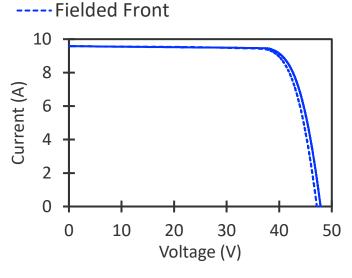
**EQE:** front surface loss - drop at short  $\lambda$ , rel. gain at long  $\lambda$ 

**IV:** Voc loss from recombination, possible passivation loss. Some Rs.

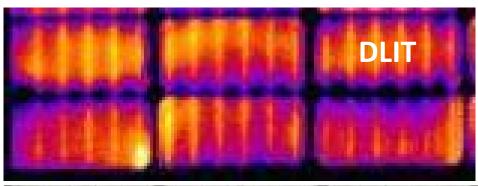
Imaging: (zoom into selected area) Some broken
grid fingers near edges.\* Local areas of high
recombination from inconsistent cell processing.\*

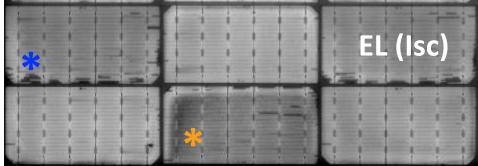


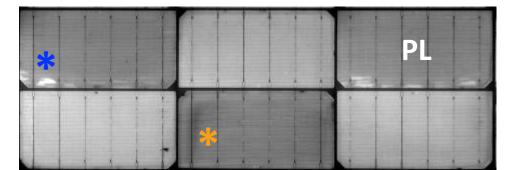




IV Results	% Change Front	% Change Rear
Isc	-0.30 %	N/A
Voc	-1.92 %	N/A
FF	-0.34 %	N/A
Pmp	-2.54 %	N/A

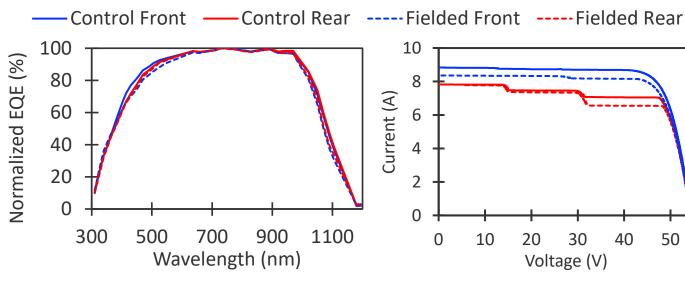


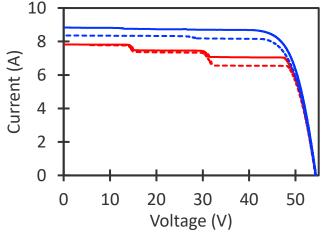


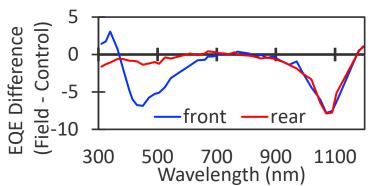


HJT, G/G, Half cell, JB center, "PE/EBA"

**EQE:** light coupling loss and recombination at both surfaces **IV:** Isc loss from encapsulant deg, Voc from surface recombination.

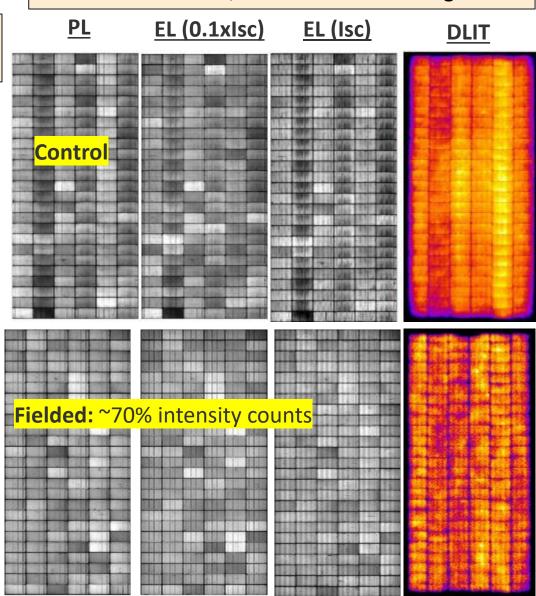






IV Results	% Change Front	% Change Rear	
Isc	-6.43 %	-3.22 %	
Voc	-1.19 %	-0.89 %	
FF	-0.02 %	-0.93 %	
Pmp	-7.53 %	-4.96 %	

**Imaging**: Luminescence intensity decreases to ~70% of the control, consistent with voltage loss.



HJT, G/G, Half cell, JB center, "PE/EBA"

**Summary:** Loss dominated by Isc likely due to unstable encapsulant and optical loss. Mismatch on rear from JBs and frame. Voc loss from carrier recombination.

**EQE:** light coupling loss both surfaces; recombination at rear

Normalized EQE (%)

300

500

**<u>IV:</u>** Isc loss from encapsulant deg, Voc from surface recombination.

Control Front — Control Rear — Fielded Front — Fielded Rear

100
80
60
40
20
Fielded Front — Fielded Rear

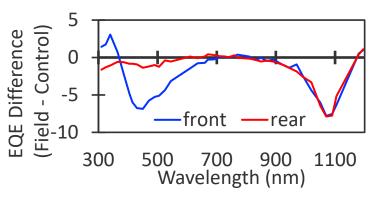
20
2

1100

0

0

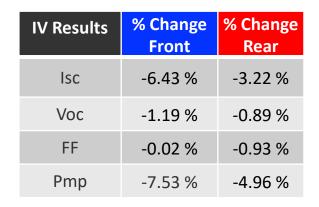
10



700

Wavelength (nm)

900



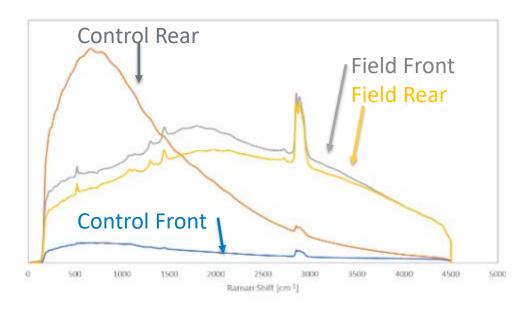
30

Voltage (V)

40

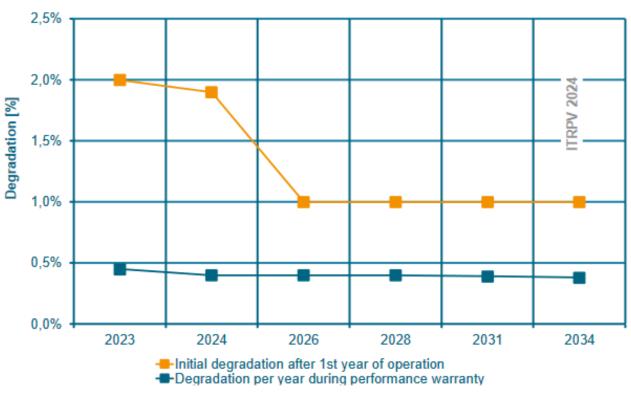
50

<u>Handheld Raman</u>: shows change in fluorescence background, consistent with additives to protect SHJ and their degradation.



## The expectation

### Degradation of c-Si PV modules



ITRPV 2024 https://www.vdma.org/international-technology-roadmap-photovoltaic

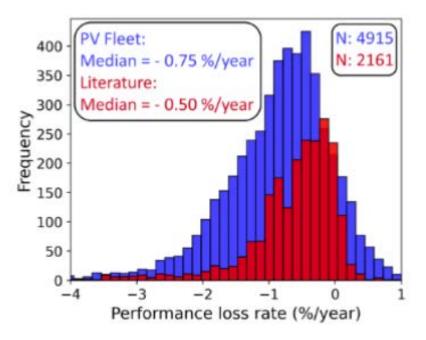


FIGURE 3 Performance loss rate distribution for the PV Fleet initiative (blue) compared with values aggregated from high-quality values (two or more measurements) from the literature (red)

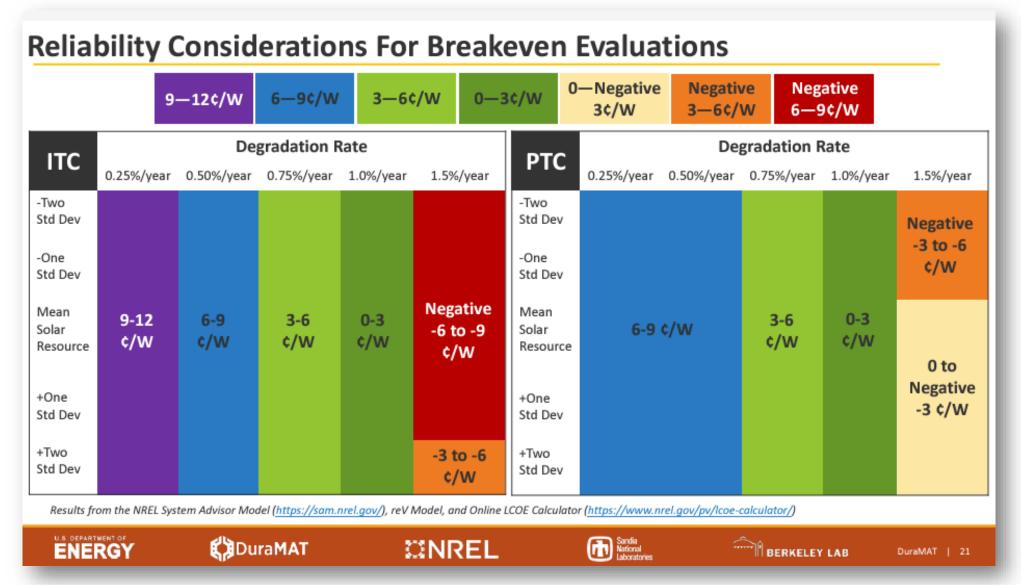
Jordan <a href="https://doi.org/10.1002/pip.3566">https://doi.org/10.1002/pip.3566</a> % bifacial systems: 0-27%?











"Reliability is every bit more consequential than the initial cost, initial efficiency and initial energy yield"

M. Woodhouse, PV Reliability Workshop 2023 https://www.nrel.gov/docs/fy24osti/85330.pdf

23

## Conclusions

After five years at NREL's Bifacial Experimental Single-Axis Tracked (BEST) Field, four PERC technologies showed an average bifacial gain of 5.1%, while one SHJ row showed 5.7%. Over this period, the bifacial gain has steadily declined. The Performance Loss Rates for PERC and SHJ technologies are -0.94% and -1.46% respectively, compared to -0.34% for monofacial

- The weathered modules exhibit a significant decrease in luminescence intensity, suggesting a comprehensive loss in module efficiency and voltage, with specific concerns about fill factor reduction due to broken grid fingers and lower current densities.
- Predominant losses on the front side, with worse outcomes for bifacial technologies.
- External Quantum Efficiency (EQE) shows more significant drop at short wavelengths.
- Imaging techniques highlight broken grid fingers and local high recombination zones.

Bifacial Experimental Single-Axis Tracked (BEST) Field at NREL

- Performance Data Available on Duramat Datahub https://datahub.duramat.org/project/about/nrel-bifacial-experimental-single-axis-tracking-field
- New data from this research added on Duramat: https://datahub.duramat.org/dataset/best-field-degradation-research

1-hr deep dive webinar into this material:

https://tinyurl.com/Duramat2024Ovaitt











NREL/PR-5K00-92280 silvana.ovaitt@nrel.gov

www.nrel.gov

https://datahub.duramat.org/project/about/best-field-degradation-research

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